



F-6888

Form PTO-1449 (Rev. 7-80) 42-44F (F-49)		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No.: F-6888		Serial No.: 09/801,990	
INFORMATION DISCLOSURE CITATION (Use several sheets if necessary)				Applicant: Yasuo TARUI, et al.		Filing Date: March 8, 2001	
				Group: 2818			
U.S. PATENT DOCUMENTS							
Examiner Initial		Document Number	Date	Name	Class	Subclass	Filing Date if Appropriate
UH		5,978,253	11/2/99	Lee et al.			
UH		6,025,627	2/15/00	Forbes et al.			
UH		5,990,515	11/23/99	Liu et al.			
FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Subclass	Translation
							Yes No
UH		0 940 856	9/8/99	EP			N <sup>F</sup>
TRANSLATION KEY: * English Abstract. <sup>F</sup> Concise statement of relevance provided in foreign search report. <sup>C</sup> Concise statement of relevance provided in specification. <sup>S</sup> Concise statement of relevance provided in IDS. <sup>P</sup> Relevant portion of reference translated. <sup>O</sup> English abstract only - copy of reference in pct search.							
OTHER INFORMATION DISCLOSURE CITATIONS (Including Author, Title, Date, Pertinent Pages, Etc.)							
UH		"Electrical Properties of MFIS-and MFMIS-FETs Using Ferroelectric SrBi <sub>2</sub> Ta <sub>2</sub> O <sub>9</sub> Film and SrTa <sub>2</sub> O <sub>6</sub> /SiON Buffer Layer" Extended Abstracts of the International Conference on Solid State Devices and Materials, Japan Society of Applied Physics, Tokyo, Japan; 1999, pages 404-405, XP000935143; *page 405; figure 1*					
EXAMINER	[Signature]			DATE CONSIDERED 03/26/04			
EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.							